

#### **General Description**

The WST4045 is the highest performance trench P-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WST4045 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

## **Product Summery**

BVDSS	RDSON	ID
-40V	73mΩ	-4.3A

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter.
- Networking DC-DC Power System
- Load Switch

#### SOT-23-3L Pin Configuration



## **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
V <sub>DS</sub>	Drain-Source Voltage	-40	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ -10V	-4.3	А	
I <sub>DP</sub>	Pulsed Drain Current	-20	A	
PD	Total Power Dissipation	2.0	W	
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 to 150	°C	

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient		125	°C/W



WST4045

**P-Ch MOSFET** 

# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-40			V
$\triangle BV_{DSS} / \triangle T_J$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$ , I_D=-1mA		-0.03		V/℃
Baaraa	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V , I <sub>D</sub> =-3A		73	85	mΩ
R <sub>DS(ON)</sub>		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-1A		98	126	
V <sub>GS(th)</sub>	Gate Threshold Voltage		-1.0	-1.5	-3.0	V
$ riangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient			4.56		mV/℃
la se	Drain Source Lookage Current	$V_{DS}$ =-28V , $V_{GS}$ =0V , $T_{J}$ =25 $^{\circ}$ C			1	- uA
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =-28V , $V_{GS}$ =0V , TJ=55 $^{\circ}$ C			5	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm 20V$ , $V_{DS}$ = $0V$			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-3A		10		S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		3.8		Ω
Qg	Total Gate Charge (-4.5V)			14		
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-20V , V <sub>GS</sub> =-10V , I <sub>D</sub> =-3.1A		2.9		nC
Q <sub>gd</sub>	Gate-Drain Charge			3.8		
T <sub>d(on)</sub>	Turn-On Delay Time			9		
Tr	Rise Time	V <sub>DD</sub> =-20V , V <sub>GS</sub> =-10V ,		8		
T <sub>d(off)</sub>	Turn-Off Delay Time	R <sub>G</sub> =3Ω, R∟=2Ω		28		ns
T <sub>f</sub>	Fall Time			10		
C <sub>iss</sub>	Input Capacitance			650		
Coss	Output Capacitance	V <sub>DS</sub> =-20V , V <sub>GS</sub> =0V , f=1MHz		90		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			70		

## **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>	$V_G = V_D = 0V$ , Force Current			-4.3	А
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =-2.5A			-1.2	V

Note :

**1.** Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

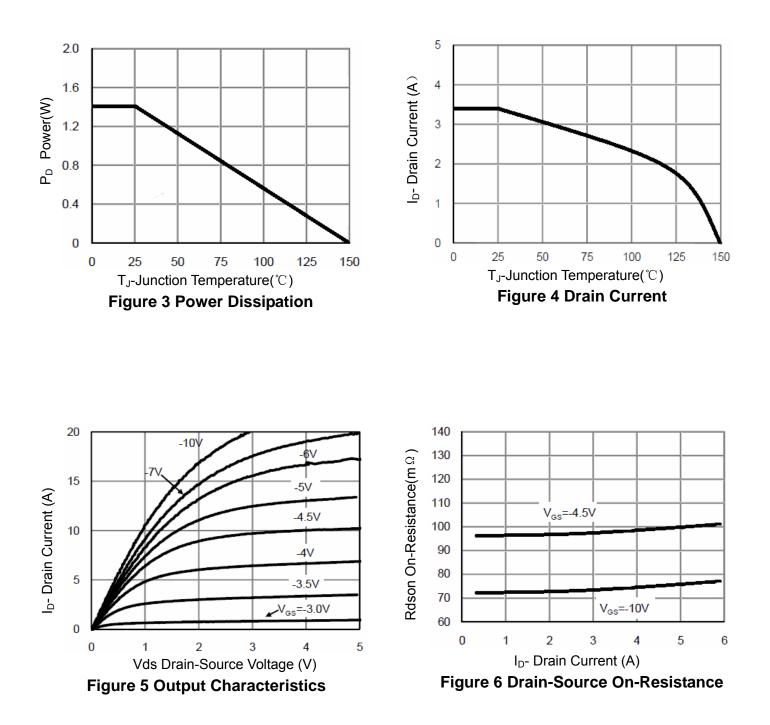
4. Guaranteed by design, not subject to production



WST4045

**P-Ch MOSFET** 

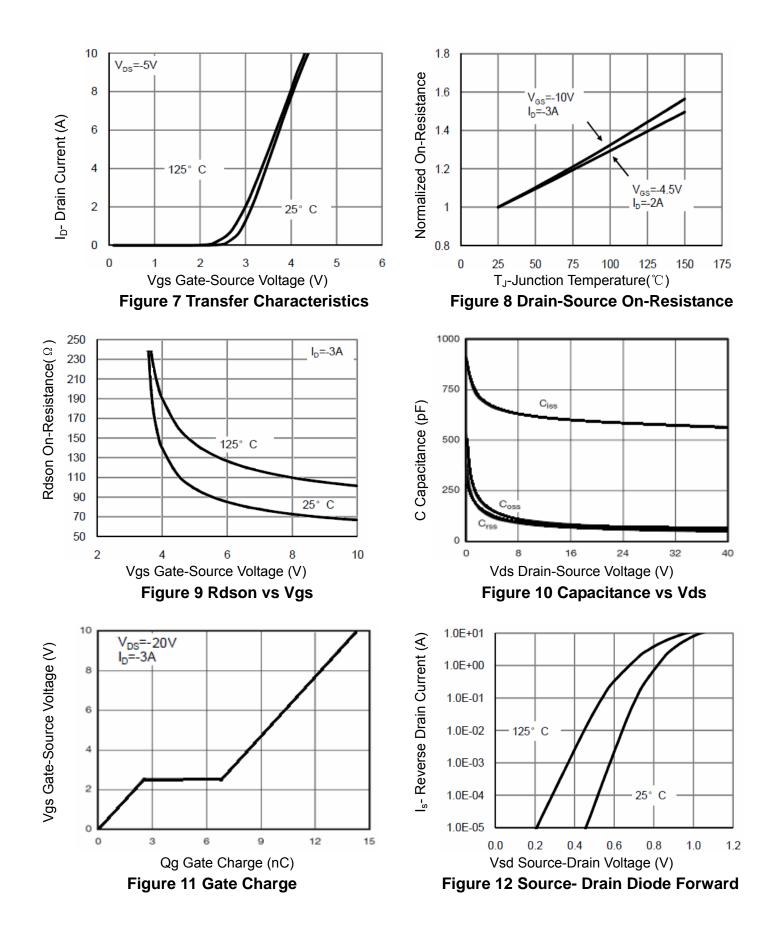
# **Typical Electrical and Thermal Characteristics**





WST4045

P-Ch MOSFET







P-Ch MOSFET

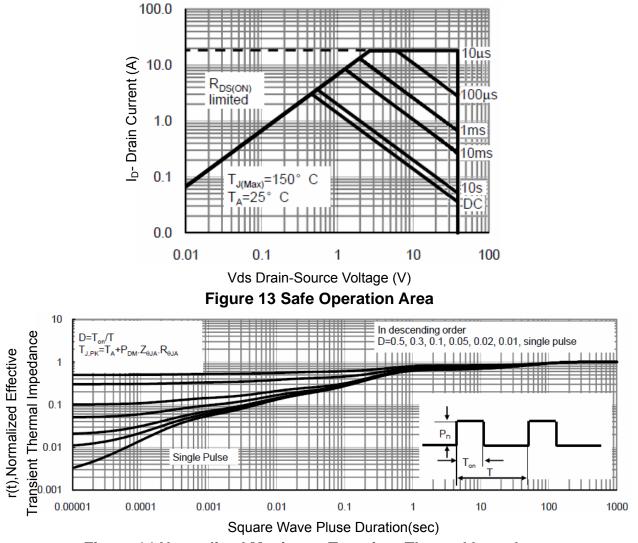


Figure 14 Normalized Maximum Transient Thermal Impedance



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